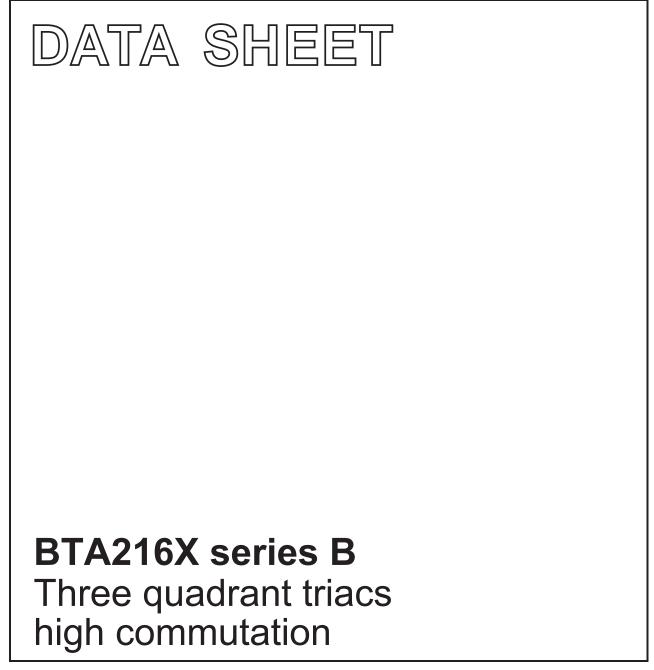
DISCRETE SEMICONDUCTORS



Product specification

September 2019



BTA216X series B

GENERAL DESCRIPTION

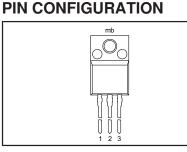
Planar passivated high commutation triacs in a full pack, plastic envelope intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. These devices will commutate the full rated rms current at the maximum rated junction temperature, without the aid of a snubber.

PINNING - SOT186A

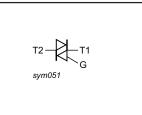
PIN	DESCRIPTION		
1	main terminal 1		
2	main terminal 2		
3	gate		
case	isolated		

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V _{DRM} I _{T(RMS)} I _{TSM}	BTA216X- Repetitive peak off-state voltages RMS on-state current Non-repetitive peak on-state current	500B 500 16 140	600B 600 16 140	800B 800 16 140	V AA



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
V _{DRM}	Repetitive peak off-state voltages		-	-500 500 ¹	-600 600 ¹	-800 800	v
I _{T(RMS)}	RMS on-state current	full sine wave;	-		16		A
I _{TSM}	Non-repetitive peak on-state current	$\begin{array}{l} T_{hs} \leq 38 \ ^{\circ}\text{C} \\ \text{full sine wave;} \\ T_{j} = 25 \ ^{\circ}\text{C} \text{ prior to} \\ \text{surge} \\ t = 20 \ \text{ms} \end{array}$	_		140		A
l ² t	I ² t for fusing	t = 16.7 ms t = 10 ms	-		150 98		A A ² s
dl _T /dt	Repetitive rate of rise of on-state current after triggering	$I_{TM} = 20 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A}/\mu \text{s}$			100		A/μs
$\begin{matrix} I_{GM} \\ V_{GM} \\ P_{GM} \\ P_{G(AV)} \end{matrix}$	Peak gate current Peak gate voltage Peak gate power Average gate power	over any 20 ms period	- - -		2 5 5 0.5		A V W W
$ \begin{array}{c} T_{stg} \\ T_{j} \end{array} $	Storage temperature Operating junction temperature	penou	-40 -		150 125		Ĵ Ĵ

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/ μ s.

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ISOLATION LIMITING VALUE & CHARACTERISTIC

 $T_{hs} = 25$ °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{isol}	R.M.S. isolation voltage from all three terminals to external heatsink	f = 50-60 Hz; sinusoidal waveform; R.H. $\leq 65\%$; clean and dustfree	-		2500	V
C _{isol}	Capacitance from T2 to external heatsink	f = 1 MHz	-	10	-	pF

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-hs} R _{th j-a}	Thermal resistance junction to heatsink Thermal resistance junction to ambient	full or half cycle with heatsink compound without heatsink compound in free air	- -	- - 55	4.0 5.5 -	K/W K/W K/W

STATIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{GT}	Gate trigger current ²	$V_{\rm D} = 12 \text{ V}; I_{\rm T} = 0.1 \text{ A}$				
GI		T2+G+	2	18	50	mA
		T2+ G-	222	21	50	mA
		T2- G-	2	34	50	mA
I ₁	Latching current	$V_{\rm D} = 12 \text{ V}; I_{\rm GT} = 0.1 \text{ A}$				
-		T2+G+	-	31	60	mA
		T2+ G-	-	34	90	mA
		T2- G-	-	30	60	mA
I _H	Holding current	$V_{\rm D} = 12 \text{ V}; I_{\rm GT} = 0.1 \text{ A}$	-	31	60	mA
İΫ _T	On-state voltage	$I_{T} = 20 \text{ A}$	-	1.2	1.5	V
V _{GT}	Gate trigger voltage	$\dot{V}_{\rm D} = 12 \text{ V}; I_{\rm T} = 0.1 \text{ A}$	-	0.7	1.5	V
		$V_{D} = 400 \text{ V}$: $I_{T} = 0.1 \text{ A}$: $T_{i} = 125 \text{ °C}$	0.25	0.4	-	V
I _D	Off-state leakage current	$V_{D} = V_{DRM(max)}; T_{j} = 125 °C$	-	0.1	0.5	mA

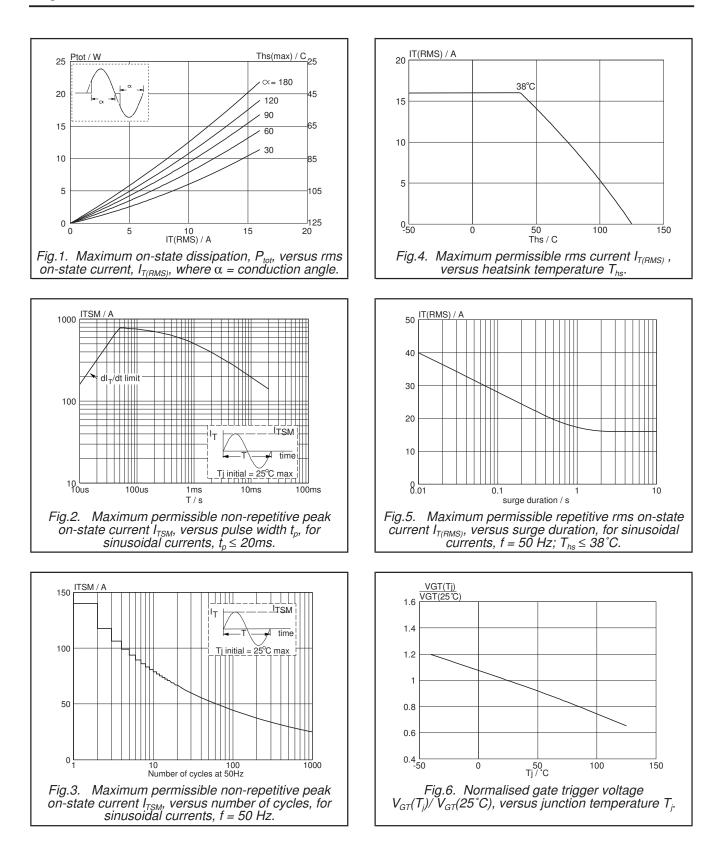
DYNAMIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

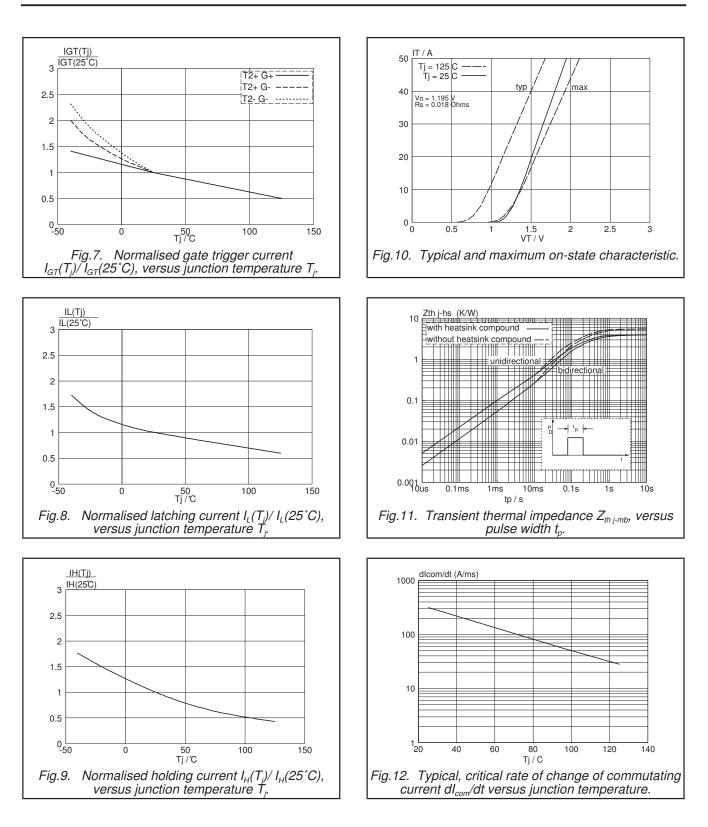
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV _D /dt	Critical rate of rise of	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125 °C;$	1000	4000	-	V/µs
dl _{com} /dt	off-state voltage Critical rate of change of commutating current	exponential waveform; gate open circuit $V_{DM} = 400 \text{ V}; T_j = 125 \text{ °C}; I_{T(RMS)} = 16 \text{ A};$ without snubber; gate open circuit	-	28	-	A/ms
t _{gt}	Gate controlled turn-on time	$I_{TM} = 20 \text{ A}; V_D = V_{DRM(max)}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu \text{s}$	-	2	-	μs

² Device does not trigger in the T2-, G+ quadrant.

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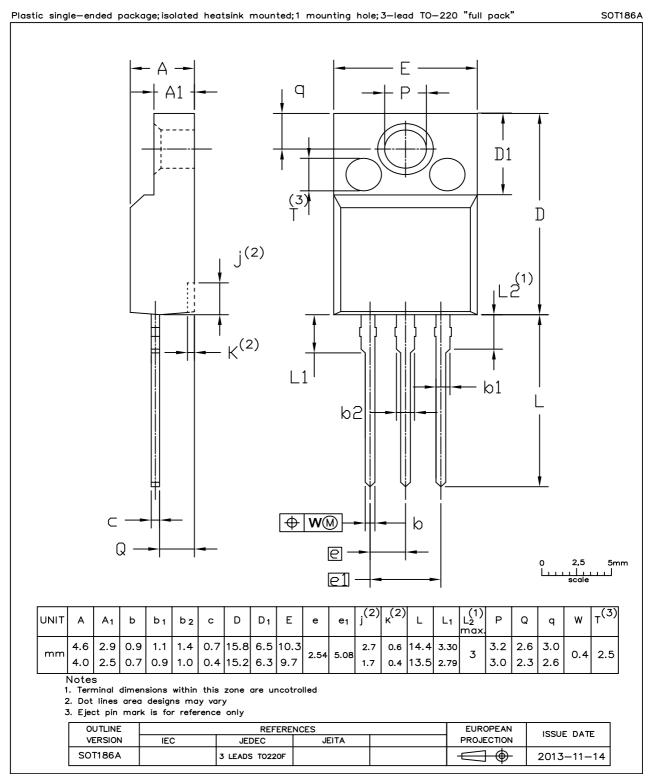


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MECHANICAL DATA



Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.ween-semi.com</u>.

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